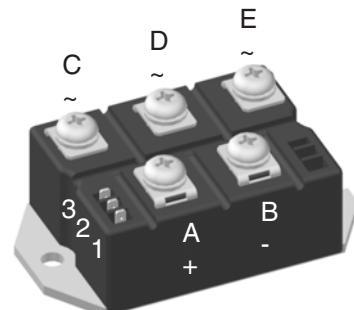
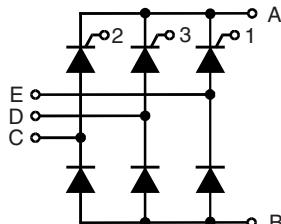


Three Phase Half Controlled Rectifier Bridge, B6HK

$I_{dAVM} = 110/167 A$
 $V_{RRM} = 1200-1600 V$

V_{RSM} V_{DSM}	V_{RRM} V_{DRM}	Type
V	V	
1300 1700	1200 1600	VVZ 110-12io7 VVZ 175-16io7



Symbol	Test Conditions	Maximum Ratings		
		VVZ 110	VVZ 175	
I_{dAV}	$T_c = 85^\circ C$; module per leg	110	167	A
I_{FRMS}, I_{TRMS}		58	89	A
I_{FSM}, I_{TSM}	$T_{VJ} = 45^\circ C$; $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1150	1500	A
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1230	1600	A
I^2t	$T_{VJ} = 45^\circ C$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1000	1350	A
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1070	1450	A
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 50 \text{ A}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, non repetitive, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$, $I_T = 1/3 \cdot I_{dAV}$	6600	11200	$A^2\text{s}$
		6280	10750	$A^2\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	5000	9100	$A^2\text{s}$
		4750	8830	$A^2\text{s}$
V_{RGM}		150	500	$A/\mu\text{s}$
P_{GM}	$T_{VJ} = T_{VJM}$ $t_p = 30 \mu\text{s}$ $I_T = I_{TAVM}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$	\leq \leq \leq	10 5 1	W
			0.5	W
P_{GAVM}		-40...+125		$^\circ\text{C}$
T_{VJ}		125		$^\circ\text{C}$
T_{VJM}		-40...+125		$^\circ\text{C}$
T_{stg}				
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$	2500	3000	$V\sim$
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$			$V\sim$
M_d	Mounting torque (M6) Terminal connection torque (M6)	5±15 %	5±15 %	Nm
Weight	typ.	300	300	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

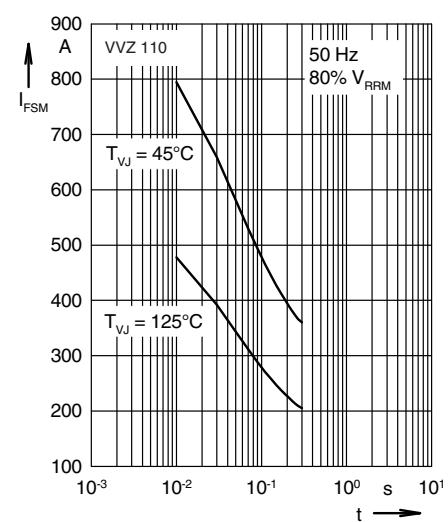
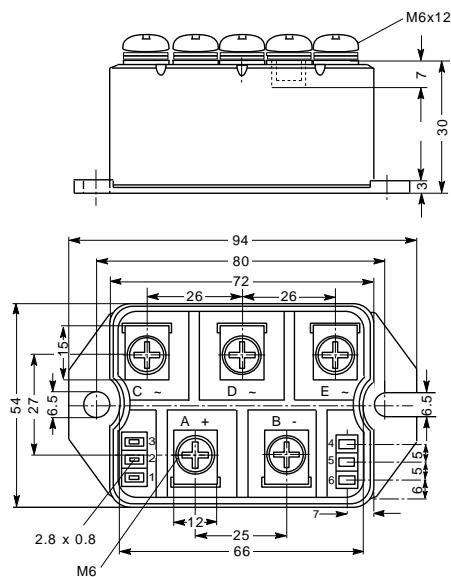
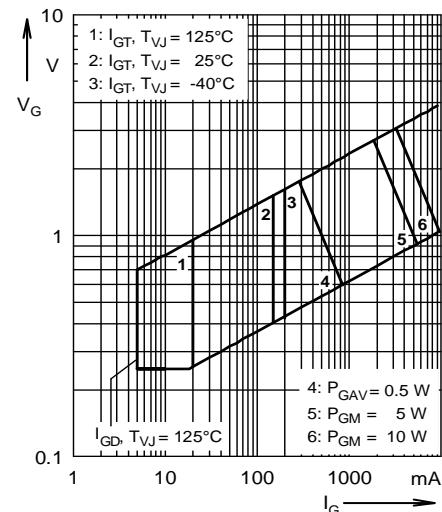
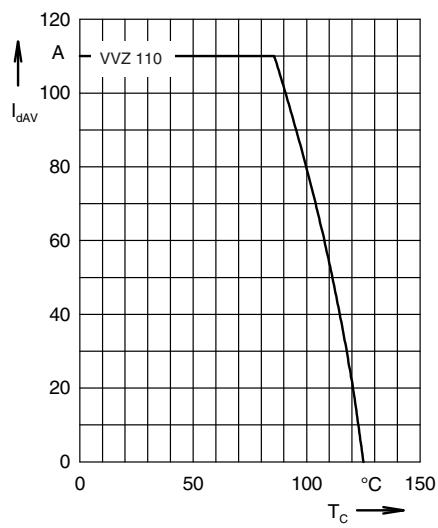
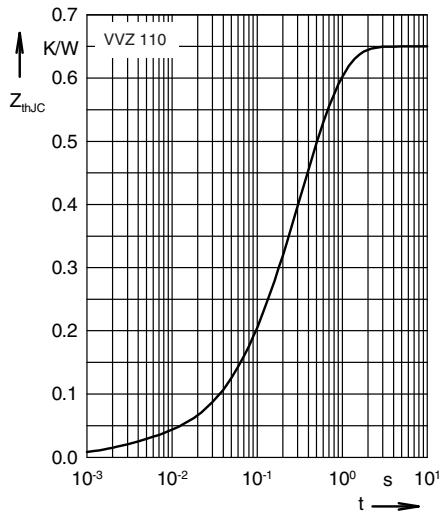
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Symbol
Test Conditions
Characteristic Values
VVZ 110 | VVZ 175

I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$	$T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ C$	\leq	5	mA
			\leq	0.3	mA
V_F, V_T	$I_F, I_T = 200 A, T_{VJ} = 25^\circ C$		\leq	1.75	V
V_{TO} r_T	For power-loss calculations only $(T_{VJ} = 125^\circ C)$		0.85	0.85	V
			6	3.5	$m\Omega$
V_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$		\leq	1.5	V
		$T_{VJ} = -40^\circ C$	\leq	1.6	V
I_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$		\leq	100	mA
		$T_{VJ} = -40^\circ C$	\leq	200	mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$		\leq	0.2	V
	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$		\leq	5	mA
I_L	$I_G = 0.3 A; t_g = 30 \mu s$	$T_{VJ} = 25^\circ C$	\leq	450	mA
	$dI_G/dt = 0.3 A/\mu s$				
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$		\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = \frac{1}{2} V_{DRM}$		\leq	2	μs
	$I_G = 0.3 A; dI_G/dt = 0.3 A/\mu s$				
R_{thJC}	per thyristor (diode); DC current		0.65	0.46	K/W
	per module		0.108	0.077	K/W
R_{thJH}	per thyristor (diode); DC current		0.8	0.55	K/W
	per module		0.133	0.092	K/W
d_s	Creeping distance on surface		10		mm
d_A	Creepage distance in air		9.4		mm
a	Max. allowable acceleration		50		m/s^2

Dimensions in mm (1 mm = 0.0394")

Fig. 3 Surge overload current
 I_{FSM} : Crest value, t: duration

Fig. 1 Gate trigger characteristics

Fig. 2 DC output current at case temperature

Fig. 4 Transient thermal impedance junction to case (per leg)